## PATENT APPLICATION

## **RESPONSE UNDER 37 CFR §1.116 EXPEDITED PROCEDURE TECHNOLOGY CENTER ART UNIT 2815**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tatsuya SHIMODA et al.

Application No.: 09/892,872 ~

Filed: June 28, 2001

For: FERROELECTRIC MEMORY AND METHOD OF MAKING THE SAME

Examiner: B. W. Baumeiste

Group Art Unit: 2815

Docket No.: 109975

AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR §1.116 of the U.S. Patent and Trademark Office ston, D.C. 20231

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

In reply to the February 11, 2003 Office Action, the period for reply being extended by the attached Petition for Extension of Time, please amend the above-identified application as follows:

## IN THE DRAWINGS:

Corrected figures are forwarded by the attached Letter to the Official Draftsperson as required by the outstanding Office Action.

## **IN THE CLAIMS:**

Please replace claims 1-3, 8-10, 12-14, 18 and 19 as follows:

1. (Three Times Amended) A ferroelectric memory, comprising:

a microstructure;

a passive matrix array that includes memory cells formed of ferroelectric capacitors, the passive matrix array being formed on the microstructure;